

TSM3457

30V P-Channel MOSFET



SOT-26

Pin Definition:

1. Drain

6. Drain

2. Drain

5. Drain

3. Gate

4. Source

Key Parameter Performance

Parameter		Value	Unit	
V_{DS}		-30	V	
R _{DS(on)} (max)	V _{GS} = -10V	60	mΩ	
	V _{GS} = -4.5V	100		
Q_g		9.52	nC	

Features

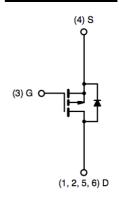
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Ordering Information

Part No.	Package	Packing
TSM3457CX6 RF	SOT-26	3kpcs / 7" Reel
TSM3457CX6 RFG	SOT-26	3kpcs / 7" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



P-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current		I _D	-5	Α
Pulsed Drain Current		I _{DM}	-20	А
Continuous Source Current (Diode Conduction	on) ^(Note 1,2)	I _S	-1.7	А
Maximum Power Dissipation	T _A =25°C	P _D	2.0	١٨/
	T _A =70°C		1.3	W
Operating Junction Temperature		TJ	+150	°C
Operating Junction and Storage Temperature	Range	T _J , T _{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R _{eJC}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R _{OJA}	80	°C/W



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Electrical Specifications (T_A = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V _{GS(TH)}	-1.0	-1.5	-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current	V _{DS} =-5V, V _{GS} = -10V	I _{D(ON)}	-20			Α
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_D = -3.7A$	-		82	100	mΩ
	$V_{GS} = -10V, I_D = -5A$	R _{DS(ON)}		50	60	
Forward Transconductance	$V_{DS} = -15V, I_{D} = -5A$	g _{fs}		10		S
Diode Forward Voltage	I _S = -1.7A, V _{GS} = 0V	V _{SD}		-0.8	-1.2	V
Dynamic (Note 4,5)						
Total Gate Charge		Q_g		9.52		
Gate-Source Charge	$V_{DS} = -15V, I_{D} = -3.7A,$ $V_{GS} = -10V$	Q_{gs}		3.43		nC
Gate-Drain Charge		Q_{gd}		1.71		
Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$	C _{iss}		551.57		
Output Capacitance		C _{oss}		90.96		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		60.79]
Switching (Note 4,5)						
Turn-On Delay Time	$V_{DD} = -15V, R_L = 15\Omega,$ $I_D = -1A, V_{GEN} = -10V,$ $R_G = 6\Omega$	t _{d(on)}		10.8		
Turn-On Rise Time		t _r		2.33		
Turn-Off Delay Time		t _{d(off)}		22.53		ns
Turn-Off Fall Time		t _f		3.87		

Notes:

- 1. Pulse width limited by the Maximum junction temperature
- 2. Surface Mounted on FR4 Board, $t \le 5$ sec.
- 3. pulse test: PW ≤300µS, duty cycle ≤2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.



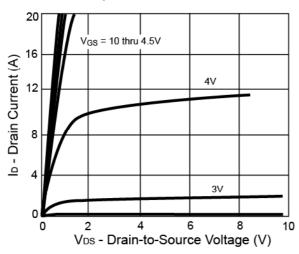
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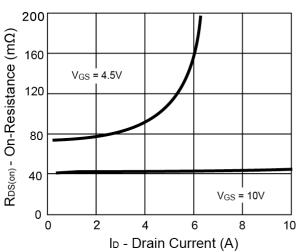


Electrical Characteristics Curves

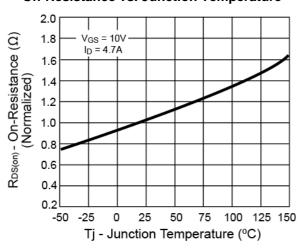
Output Characteristics



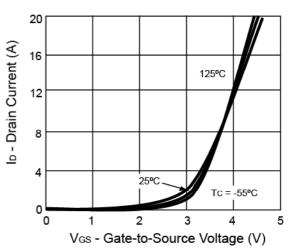
On-Resistance vs. Drain Current



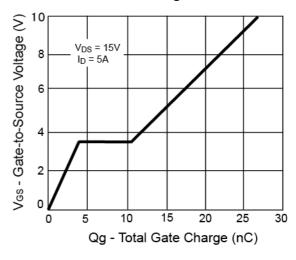
On-Resistance vs. Junction Temperature



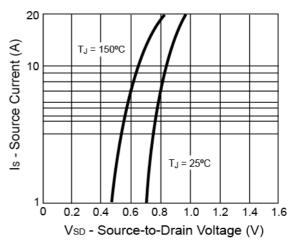
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



Version: C14

3/6



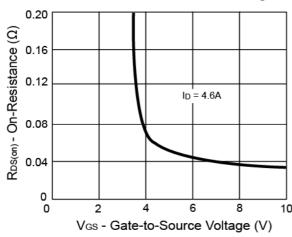
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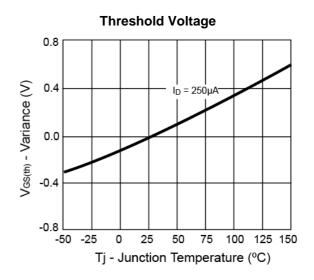
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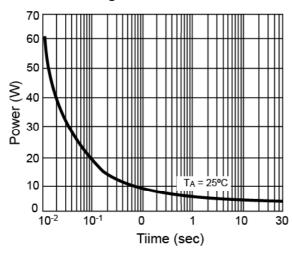
Electrical Characteristics Curves

On-Resistance vs. Gate-Source Voltage

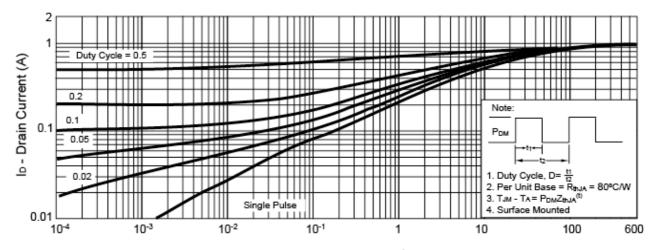




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

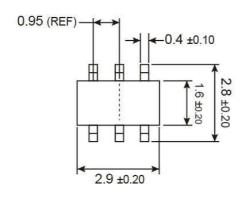


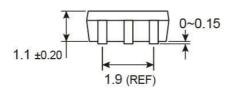
Square Wave Pulse Duration (sec)

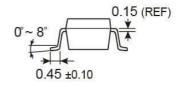




SOT-26 Mechanical Drawing







Unit: Millimeters

Marking Diagram



57 = Device Code

Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

Month Code for Halogen Free Product
 (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep,
 X=Oct, Y=Nov, Z=Dec)

L = Lot Code



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